

NPN general-purpose double transistors

Rev. 4 — 4 August 2010

Product data sheet

1. Product profile

1.1 General description

NPN general-purpose double transistors in a small SOT143B Surface-Mounted Device (SMD) plastic package.

Table 1. Product overview

Type number	Package I		PNP complement
	NXP	JEITA	
BCV63	SOT143B	-	-
BCV63B			BCV64B

1.2 Features and benefits

- Low current (max. 100 mA)
- Low voltage (max. 30 V and 6 V)
- AEC-Q101 qualified
- Small SMD plastic package

1.3 Applications

- General-purpose switching and amplification
- For use in Schmitt trigger applications

1.4 Quick reference data

Table 2. **Quick reference data** Symbol Conditions Parameter Min Тур Max Unit Per transistor collector current 100 mΑ I_{C} _ _ **Transistor TR1** open base collector-emitter voltage 30 V V_{CEO} _ - $V_{CF} = 5 V; I_{C} = 2 mA$ DC current gain h_{FF} BCV63 110 800 -BCV63B 200 _ 450



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Table 2.	Quick reference data	continued				
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
Transisto	r TR2					
V _{CEO}	collector-emitter voltage	open base	-	-	6	V
h _{FE}	DC current gain	V_{CE} = 700 mV; I _C = 2 mA	<u>[1]</u>			
	BCV63		110	-	800	
	BCV63B		200	-	450	

[1] Group selection will be done on TR1. Due to matched dies, h_{FE} values for TR2 are the same as for TR1.

2. Pinning information

Table 3.	Pinning		
Pin	Description	Simplified outline	Graphic symbol
1	collector TR2 and base TR1		
2	collector TR1		
3	emitter TR1 and TR2		
4	base TR2		

3. Ordering information

Table 4. Order	ring informa	ation	
Type number	Package		
	Name	Description	Version
BCV63	-	plastic surface-mounted package; 4 leads	SOT143B
BCV63B			

4. Marking

Table 5. Marking codes	
Type number	Marking code ^[1]
BCV63	*D5
BCV63B	*D6

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

006aab228

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5. Limiting values

Table 6. In accorda	Limiting values ance with the Absolute Maximu	m Rating System (IEC	60134).		
Symbol	Parameter	Conditions	Min	Max	Unit
Per trans	istor				
V _{EBO}	emitter-base voltage	open collector	-	6	V
I _C	collector current		-	100	mA
I _{CM}	peak collector current		-	200	mA
I _B	base current		-	100	mA
Transisto	or TR1				
V _{CBO}	collector-base voltage	open emitter	-	30	V
V _{CEO}	collector-emitter voltage	open base	-	30	V
Transisto	or TR2				
V _{CBO}	collector-base voltage	open emitter	-	6	V
V _{CEO}	collector-emitter voltage	open base	-	6	V
Per devic	e				
P _{tot}	total power dissipation	$T_{amb} \le 25 \ ^{\circ}C$	<u>[1]</u> _	250	mW
Tj	junction temperature		-	150	°C
T _{amb}	ambient temperature		-65	+150	°C
T _{stg}	storage temperature		-65	+150	°C

[1] Device mounted on an FR4 Printed-Circuit Board (PCB).

6. Thermal characteristics

Table 7.	Thermal characteristics					
Symbol	Parameter	Conditions	Min	Тур	Мах	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	<u>[1]</u> _	-	500	K/W

[1] Device mounted on an FR4 PCB.

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7. Characteristics

Symbol	Parameter	Conditions		Min	Тур	Мах	Unit
Per tran	sistor						
I _{CBO}	collector-base	V _{CB} = 30 V; I _E = 0 A		-	-	15	nA
	cut-off current	V _{CB} = 30 V; I _E = 0 A; T _j = 150 °C		-	-	5	μA
V _{CEsat}	collector-emitter saturation voltage	I _C = 10 mA; I _B = 0.5 mA		-	75	300	mV
V _{BEsat}	base-emitter saturation voltage	I _C = 10 mA; I _B = 0.5 mA	[2]	-	700	-	mV
Transist	or TR1						
h _{FE} DC current gain		V_{CE} = 5 V; I _C = 2 mA					
	BCV63			110	-	800	
	BCV63B			200	-	450	
V _{CEsat}	collector-emitter saturation voltage	I _C = 100 mA; I _B = 5 mA		-	250	650	mV
V _{BEsat}	base-emitter saturation voltage	I _C = 100 mA; I _B = 5 mA	[2]	-	850	-	mV
V _{BE}	base-emitter voltage	I_{C} = 2 mA; V_{CE} = 5 V	<u>[3]</u>	600	650	750	mV
		I_{C} = 10 mA; V_{CE} = 5 V	[3]	-	-	820	mV
f _T	transition frequency	V _{CE} = 5 V; I _C = 10 mA; f = 100 MHz		100	-	-	MHz
C _c	collector capacitance	V _{CB} = 10 V; I _E = i _e = 0 A; f = 1 MHz		-	4	-	pF
Transist	or TR2						
h _{FE}	DC current gain	V _{CE} = 700 mV; I _C = 2 mA	<u>[1]</u>				
	BCV63			110	-	800	
	BCV63B			200	-	450	
V _{CEsat}	collector-emitter saturation voltage	I _C = 100 mA; I _B = 5 mA		-	250	-	mV
V_{BE}	base-emitter voltage	I _C = 2 mA; V _{CE} = 700 mV	<u>[3]</u>	-	700	-	mV

[1] Group selection will be done on TR1. Due to matched dies, h_{FE} values for TR2 are the same as for TR1.

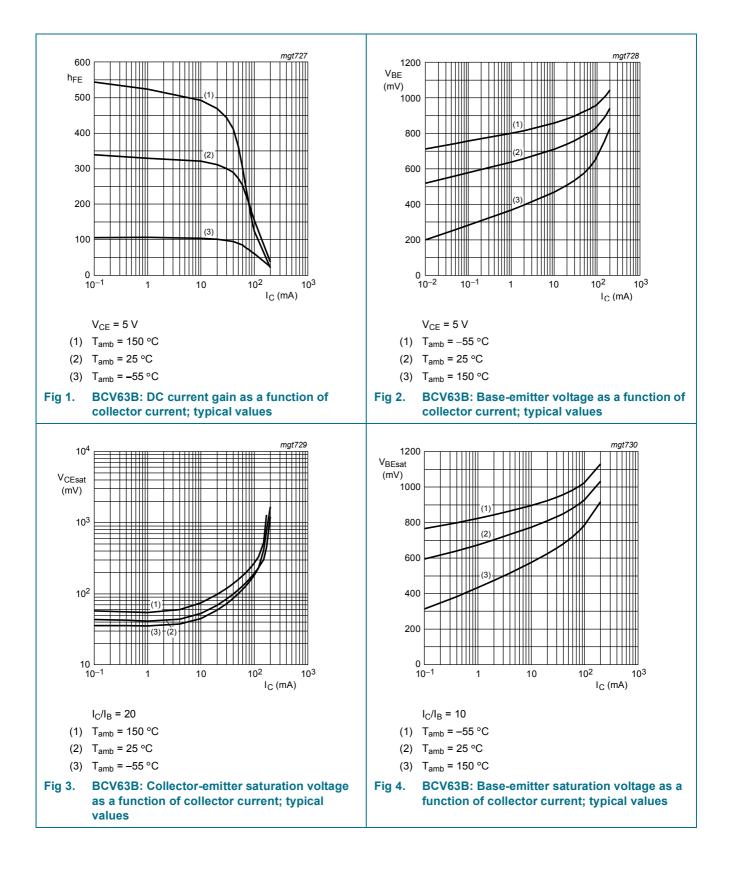
[2] V_{BEsat} decreases by about 1.7 mV/K with increasing temperature.

[3] V_{BE} decreases by about 2 mV/K with increasing temperature.

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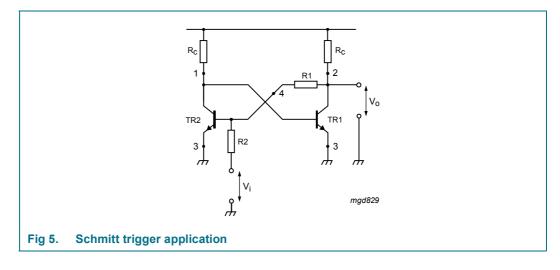
BCV63; BCV63B

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8. Application information



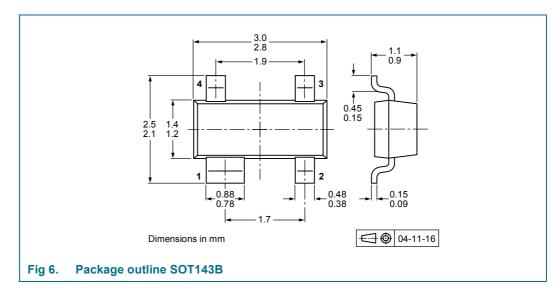
9. Test information

9.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101* - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

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10. Package outline



11. Packing information

Table 9. Packing methods

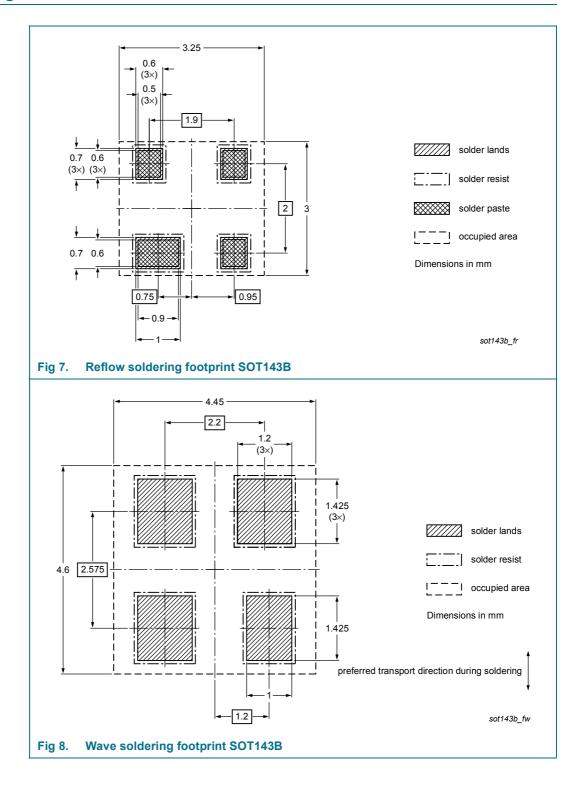
The indicated -xxx are the last three digits of the 12NC ordering code.[1]

Type number	Package	Package Description		Packing quantity	
			3000	10000	
BCV63	SOT143B	4 mm pitch, 8 mm tape and reel	-215	-235	
BCV63B					

[1] For further information and the availability of packing methods, see <u>Section 14</u>.

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12. Soldering



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13. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes		
BCV63_63B v.4	20100804	Product data sheet	-	BCV63_BCV63B_3		
Modifications:		of this data sheet has been of NXP Semiconductors.	redesigned to comply v	vith the new identity		
	 Legal texts 	have been adapted to the n	iew company name whe	ere appropriate.		
	<u>Section 1 "Product profile"</u> : amended					
	<u>Section 3 "Ordering information"</u> : added					
	 Section 4 "N 	<u>/larking"</u> : updated				
	 Figure 1, 2, 	3 and 4: added				
	<u>Section 8 "Application information": added</u>					
	<u>Section 9 "Test information"</u> : added					
	 Figure 6: superseded by minimized package outline drawing 					
	 <u>Section 11 "Packing information"</u>: added 					
	Section 12	<u>'Soldering"</u> : added				
	Section 14	<u>'Legal information</u> ": updated	b			
BCV63_BCV63B_3	19990521	Product specification	-	BCV63_CNV_2		
BCV63 CNV 2	19970310	Product specification	-	-		

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14. Legal information

14.1 Data sheet status

Document status[1][2]	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Date of release: 4 August 2010 Document identifier: BCV63_63B